

FIG.1

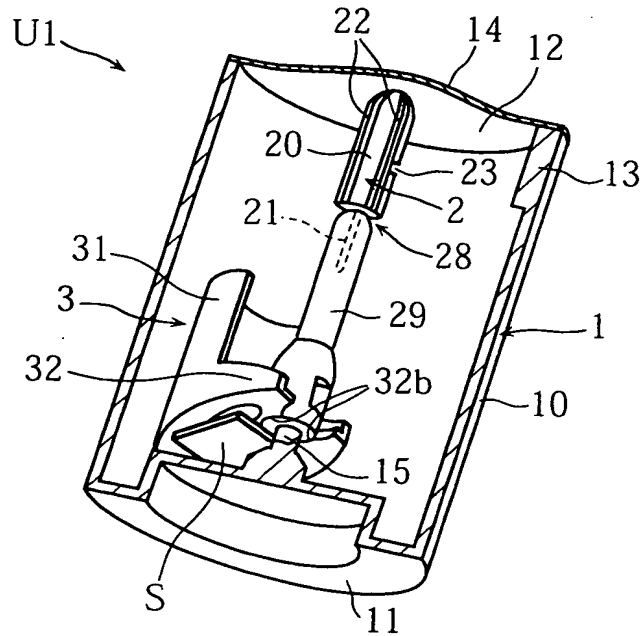


FIG.2

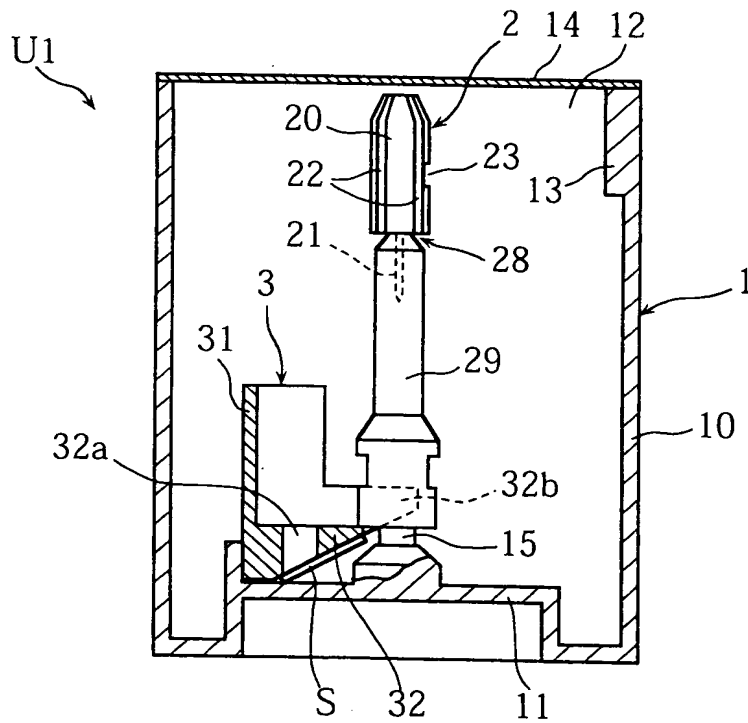


FIG.3A

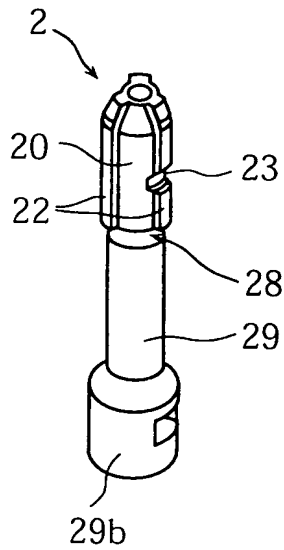


FIG.3B

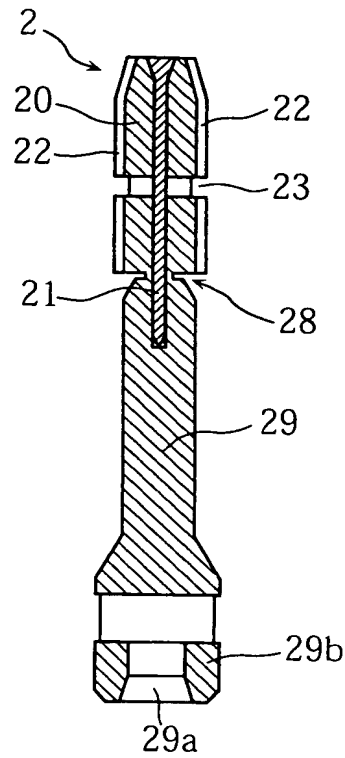


FIG.4

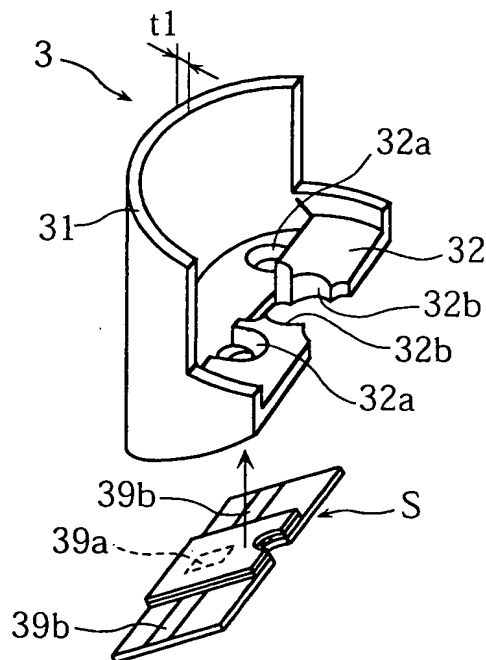


FIG.5A

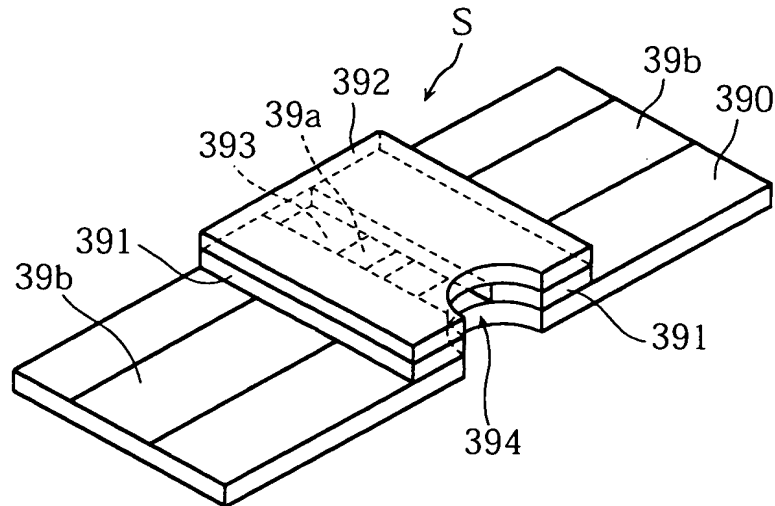


FIG.5B

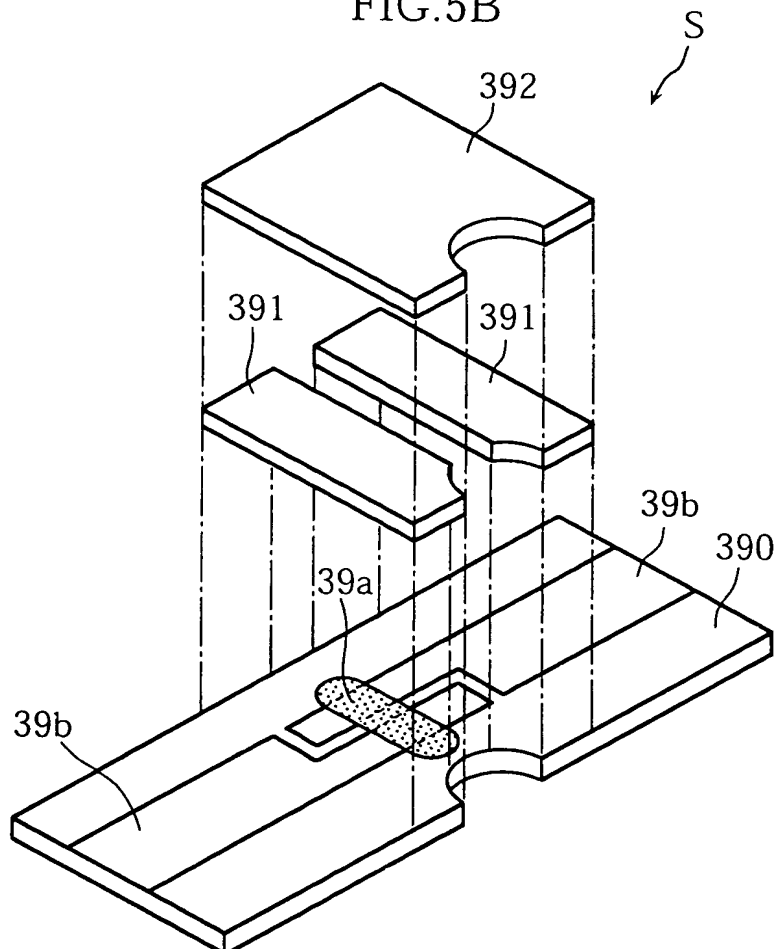


FIG.6

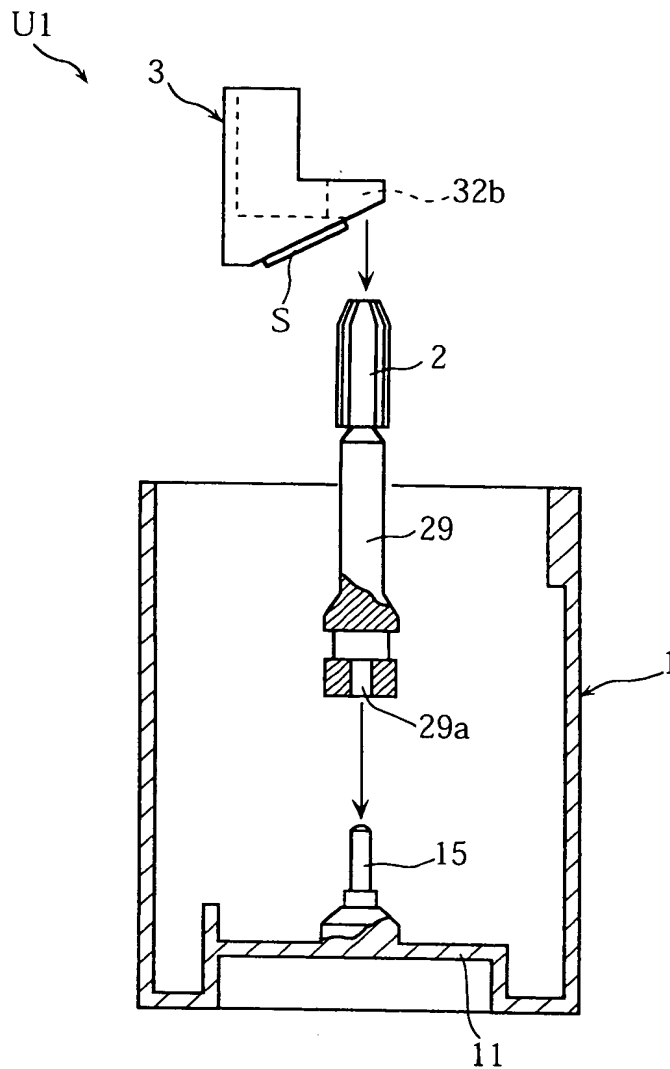


FIG. 7

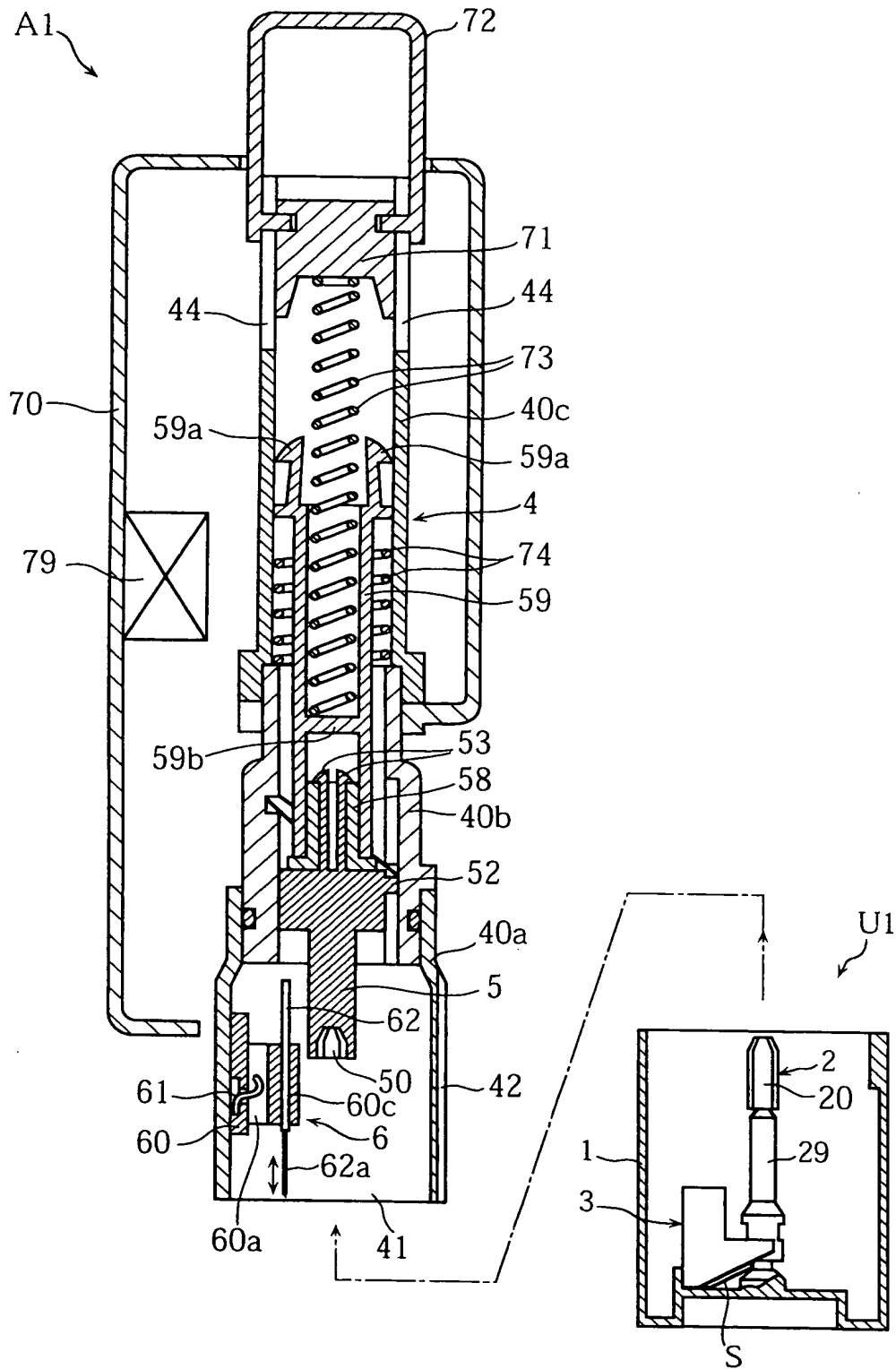




FIG.9

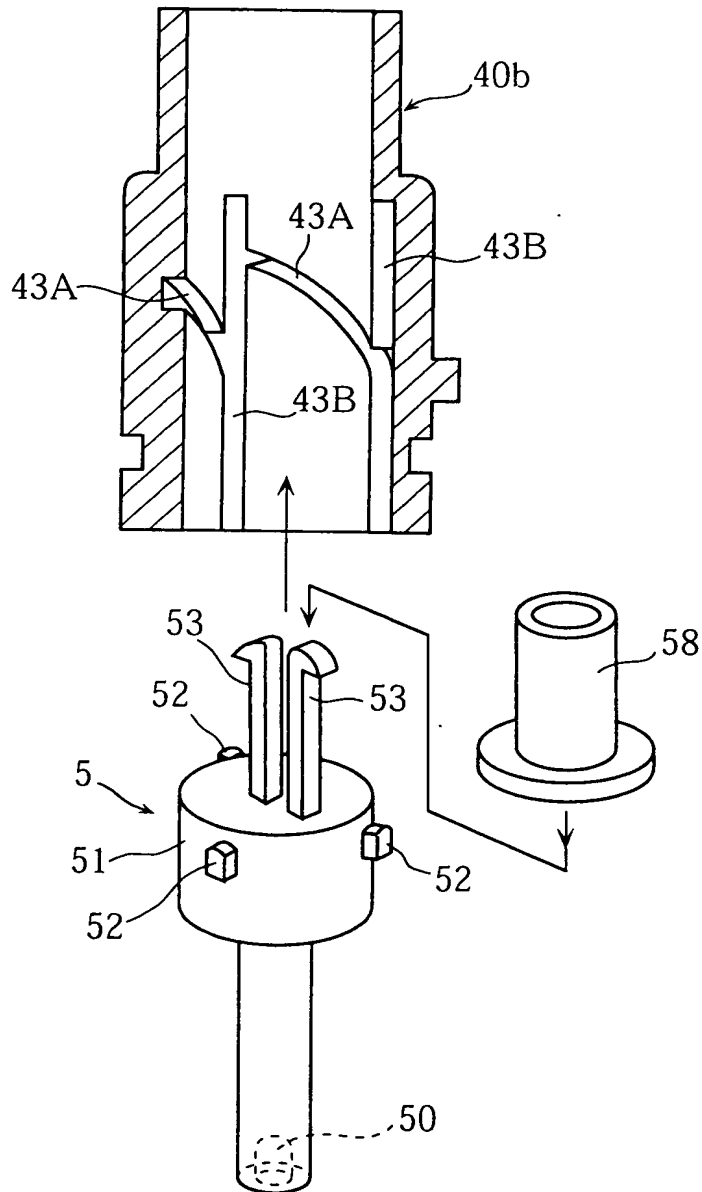


FIG.10A

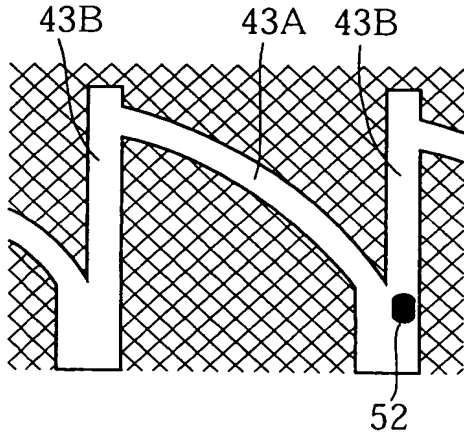


FIG.10B

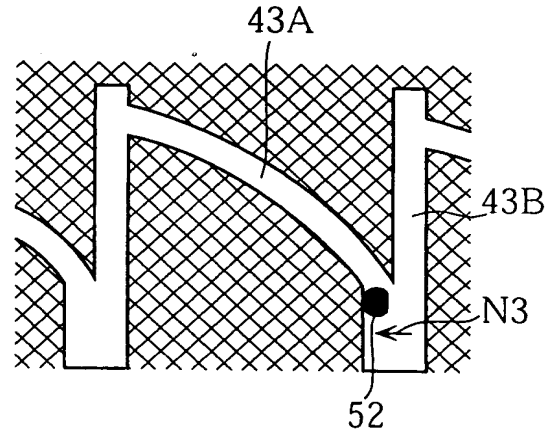


FIG.10C

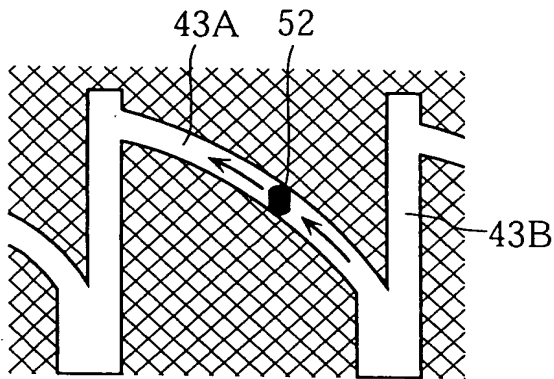


FIG.10D

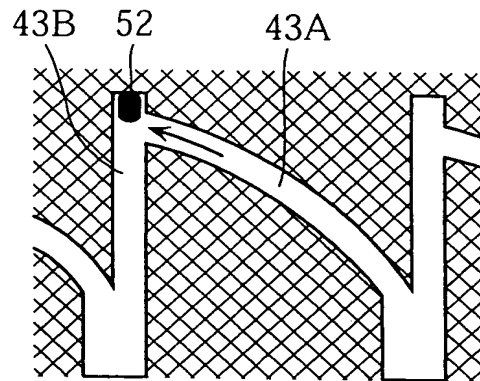


FIG.10E

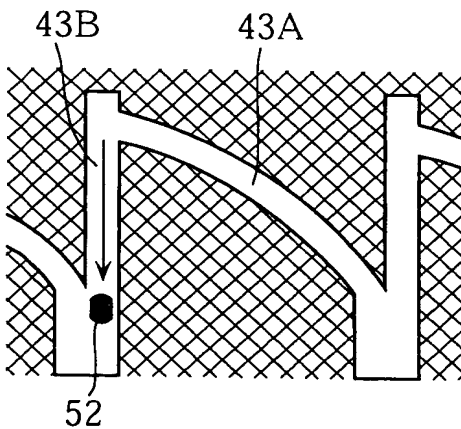




FIG. 11

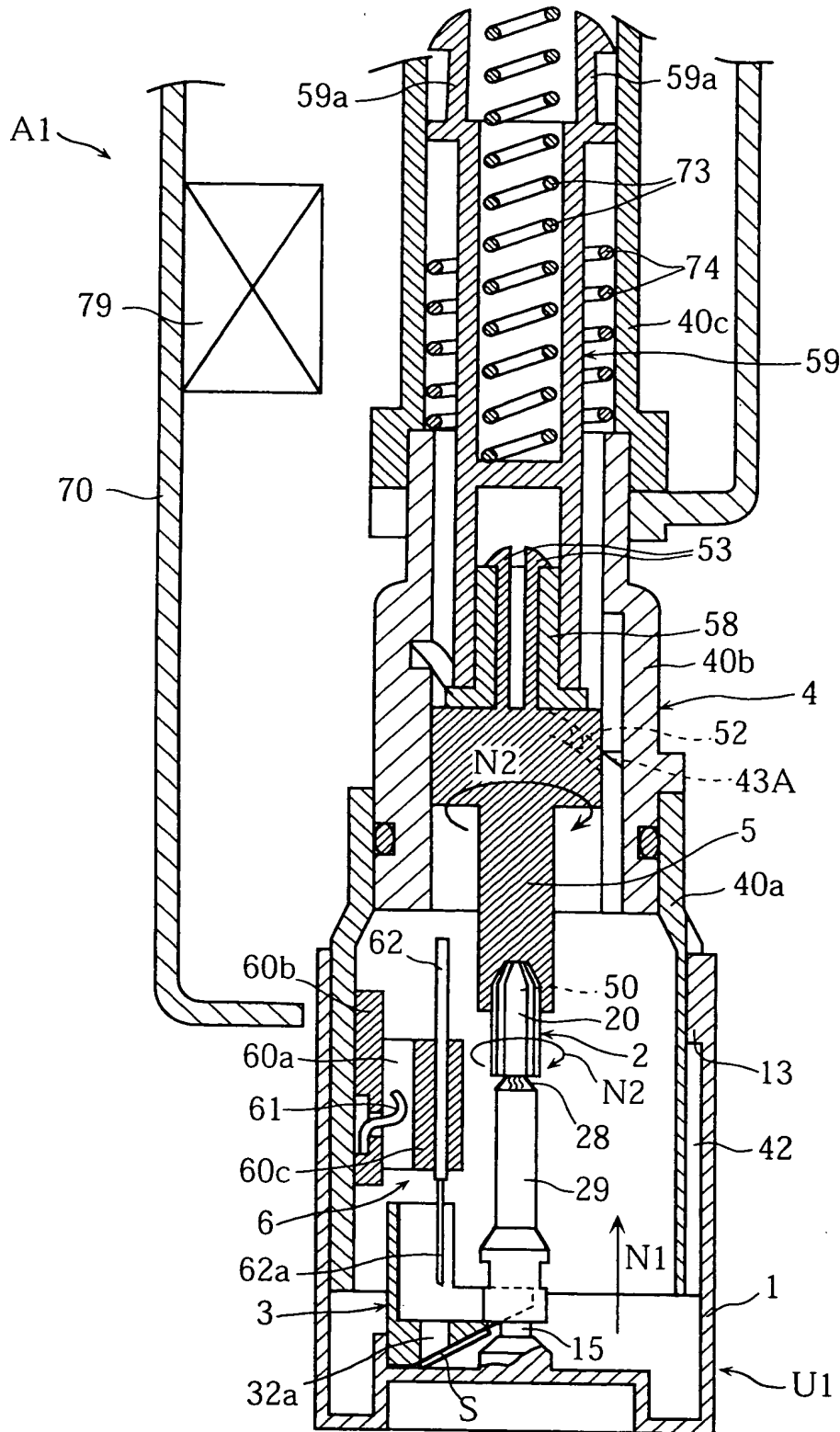








FIG.15

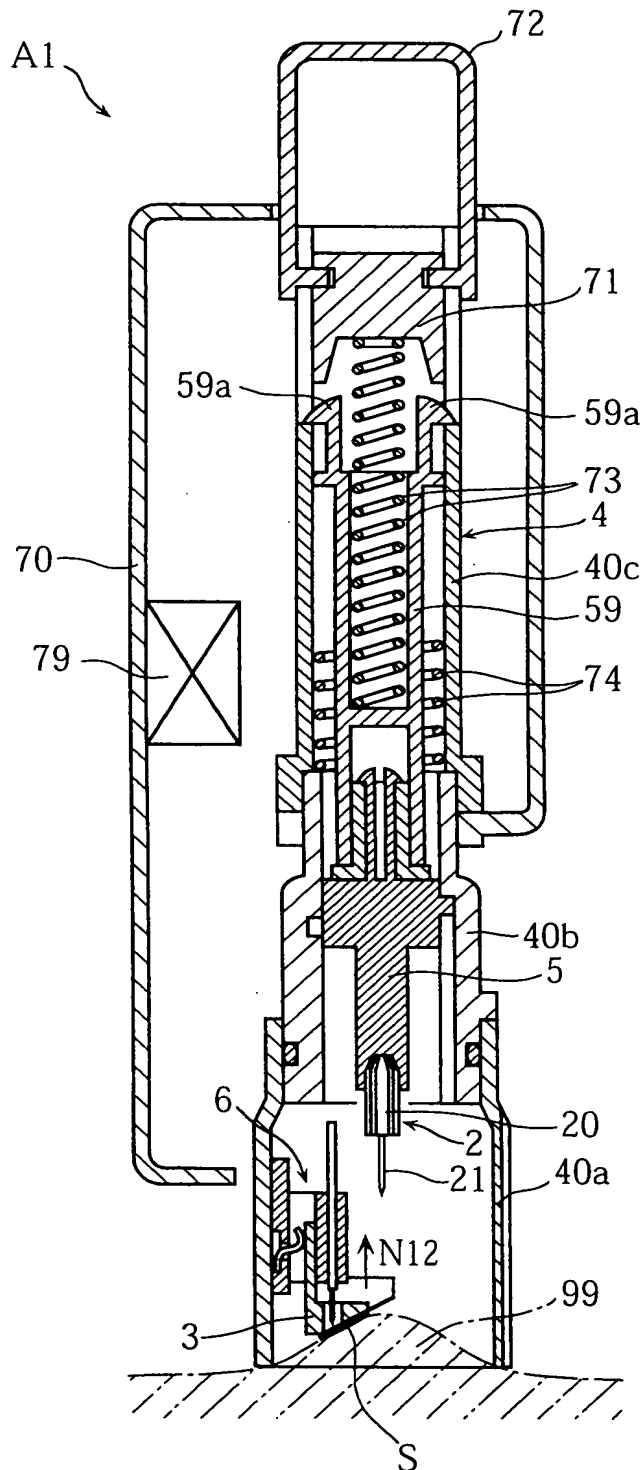


FIG.16

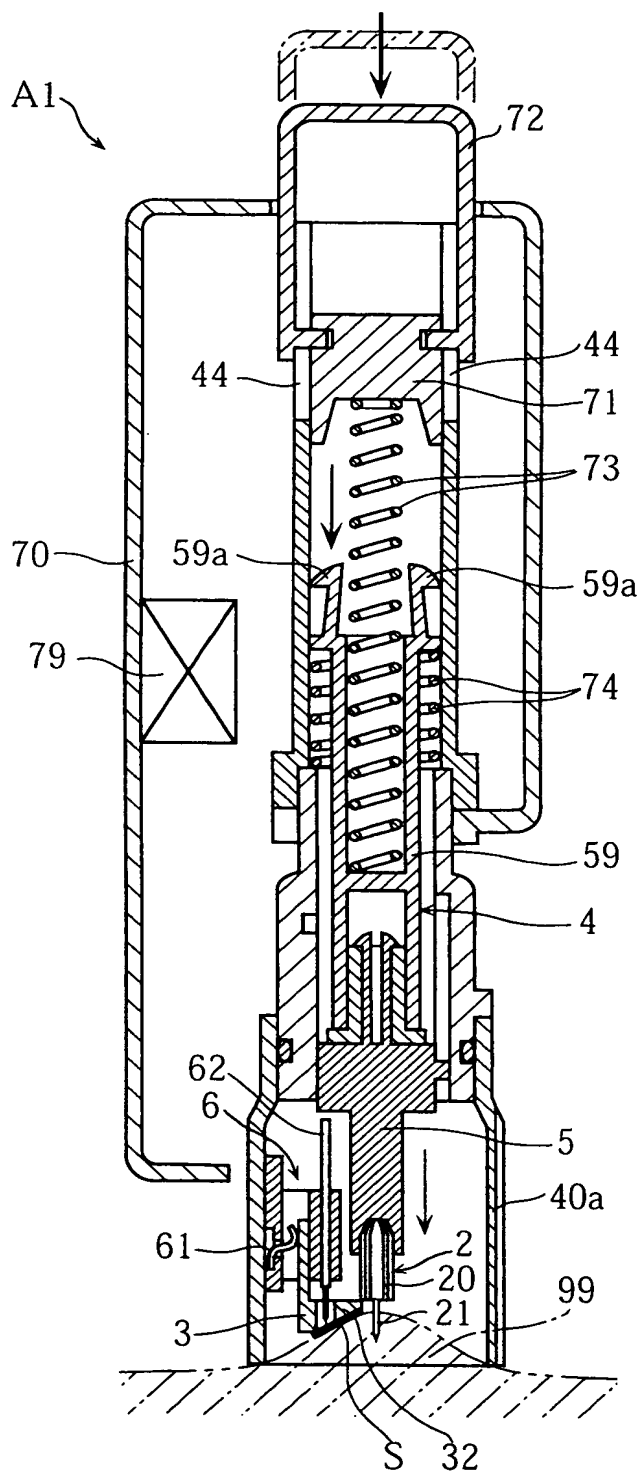


FIG.17

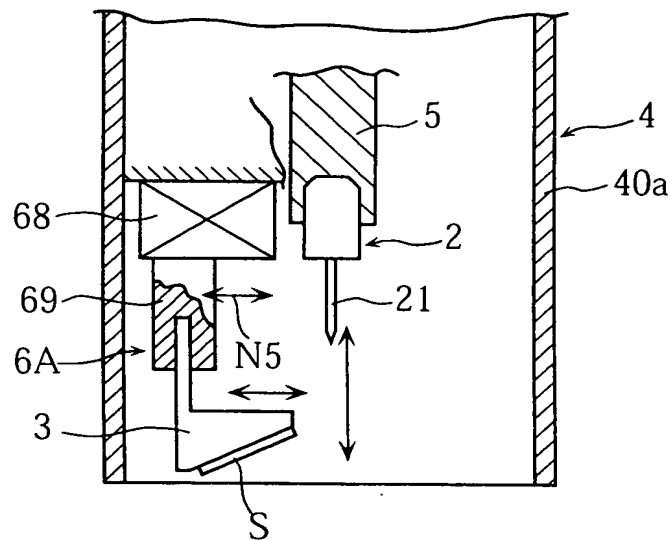
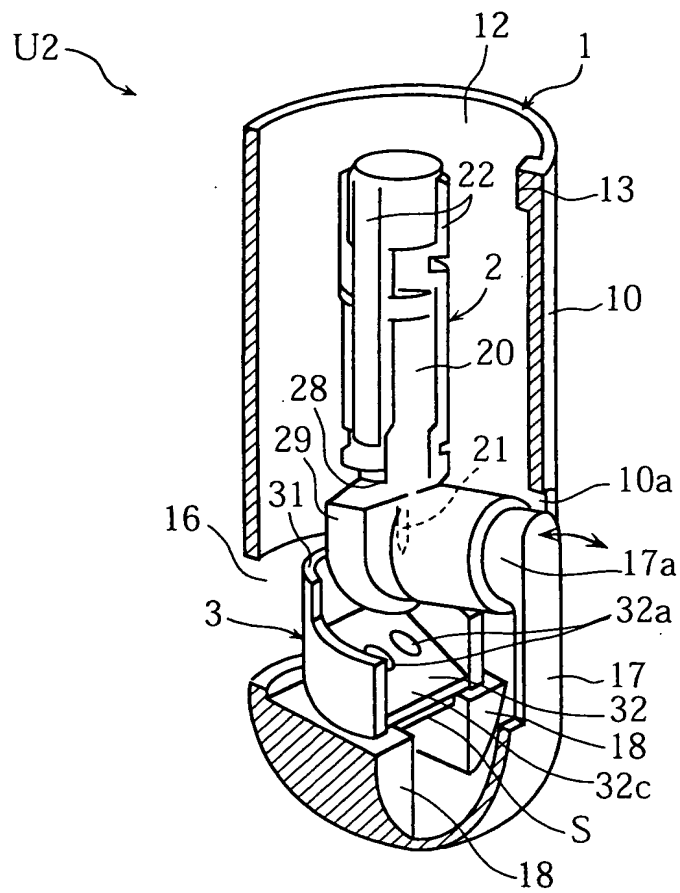


FIG.18





[illegible]

FIG.20

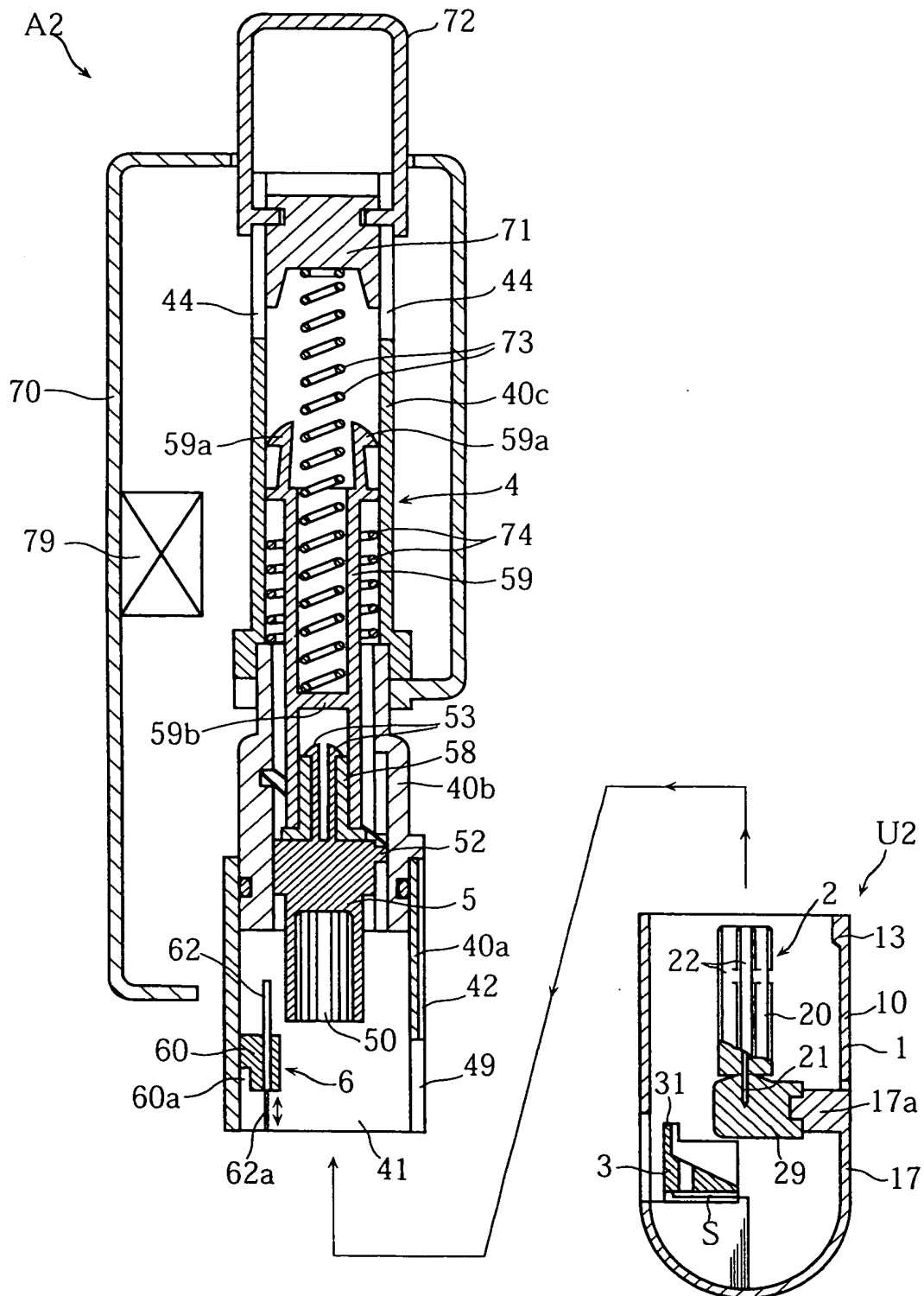
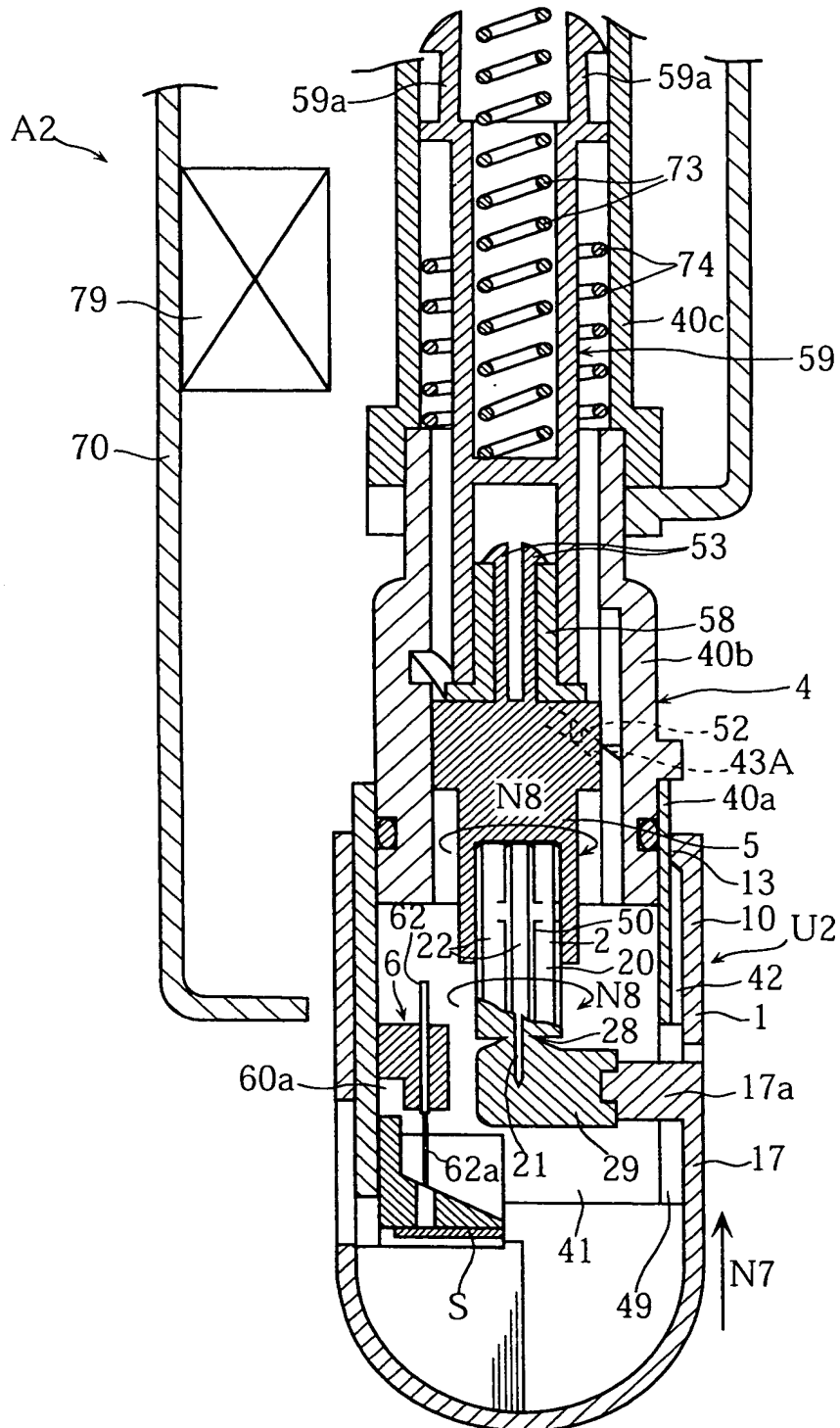


FIG.21



A detailed cross-sectional diagram of a semiconductor device. The device features a substrate 11 at the base, which supports a layer 18. Above layer 18 is a large rectangular block 49. To the left of block 49 is a vertical structure 6, which includes a central core 60 and surrounding layers 62 and 62a. A thin layer 3 is positioned between the substrate 11 and the lower part of structure 6. A horizontal layer 31 is located above layer 3. A complex structure 29 is situated to the right of structure 6, featuring a sloped surface 32 and a top layer 32c. Above structure 29 is a layer 17a, which is part of a larger layer 17. A vertical channel or opening 41 passes through several layers, including 17, 17a, 10a, 10, U2, 13, and 42. The top of the device is capped by a layer 40b, with a side wall 40a on the left. Various other layers and interfaces are labeled with numbers like 1, 2, 20, 21, 22, 50, and 5. The entire assembly is enclosed within a container-like structure indicated by A2.

FIG. 23

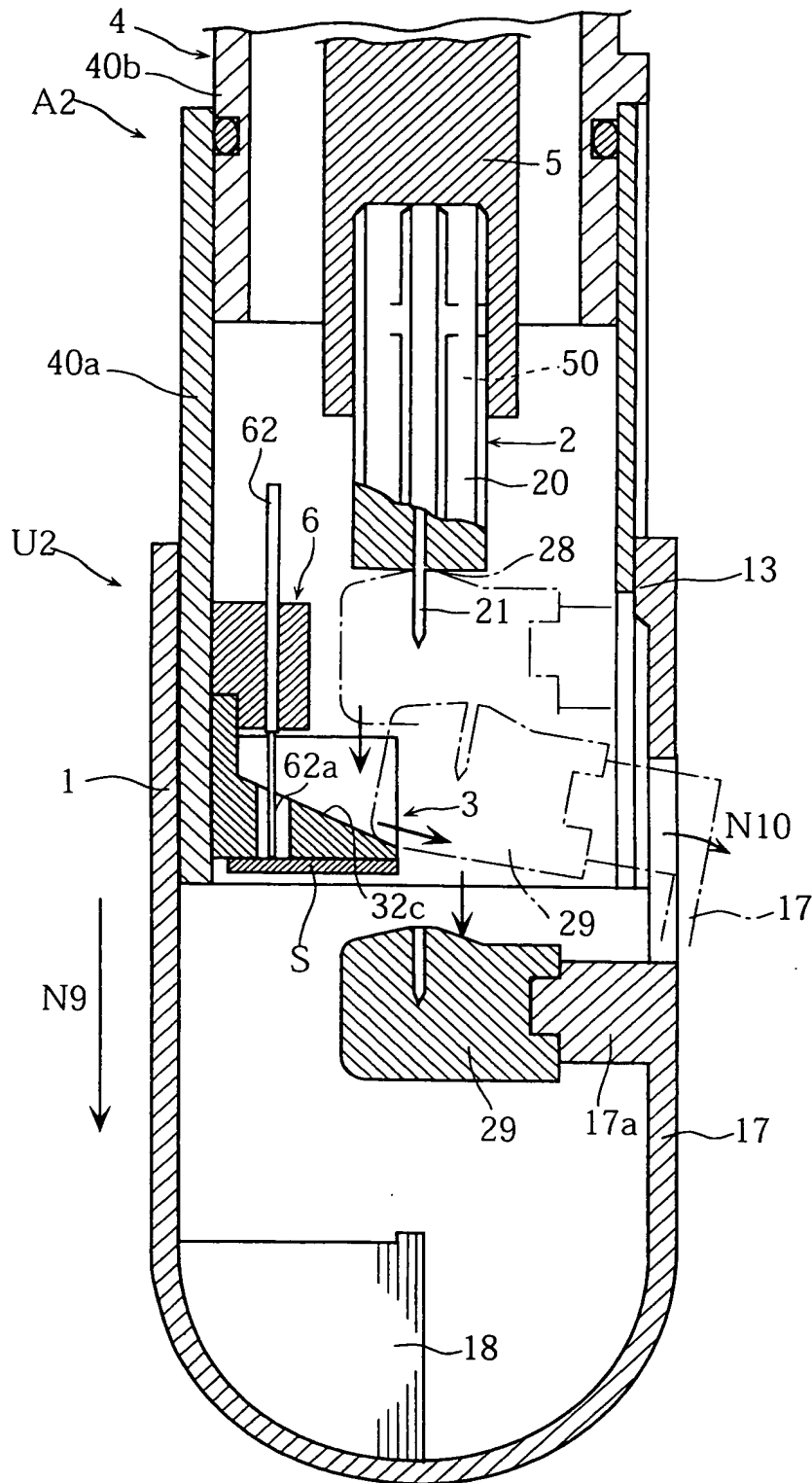


FIG.24

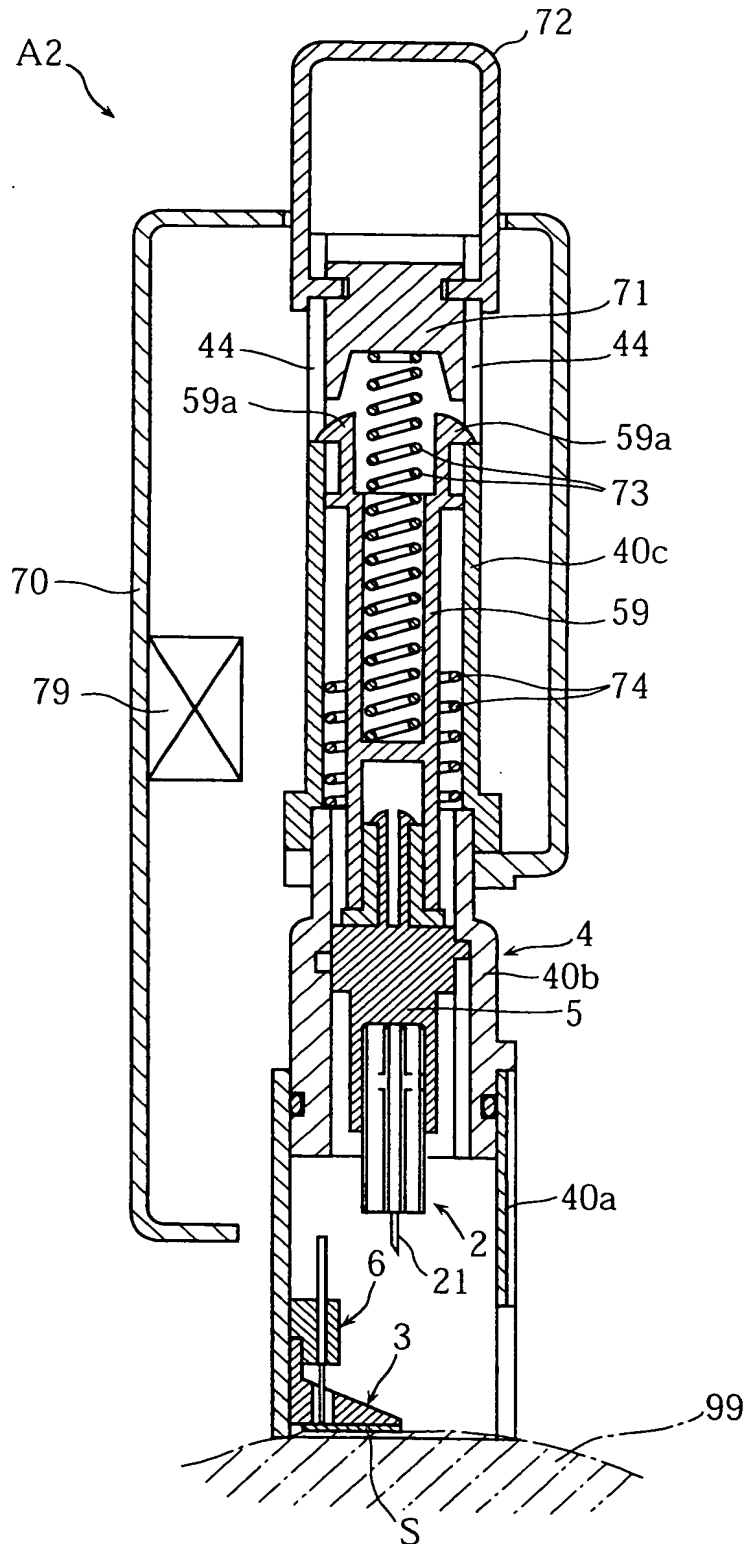


FIG. 25

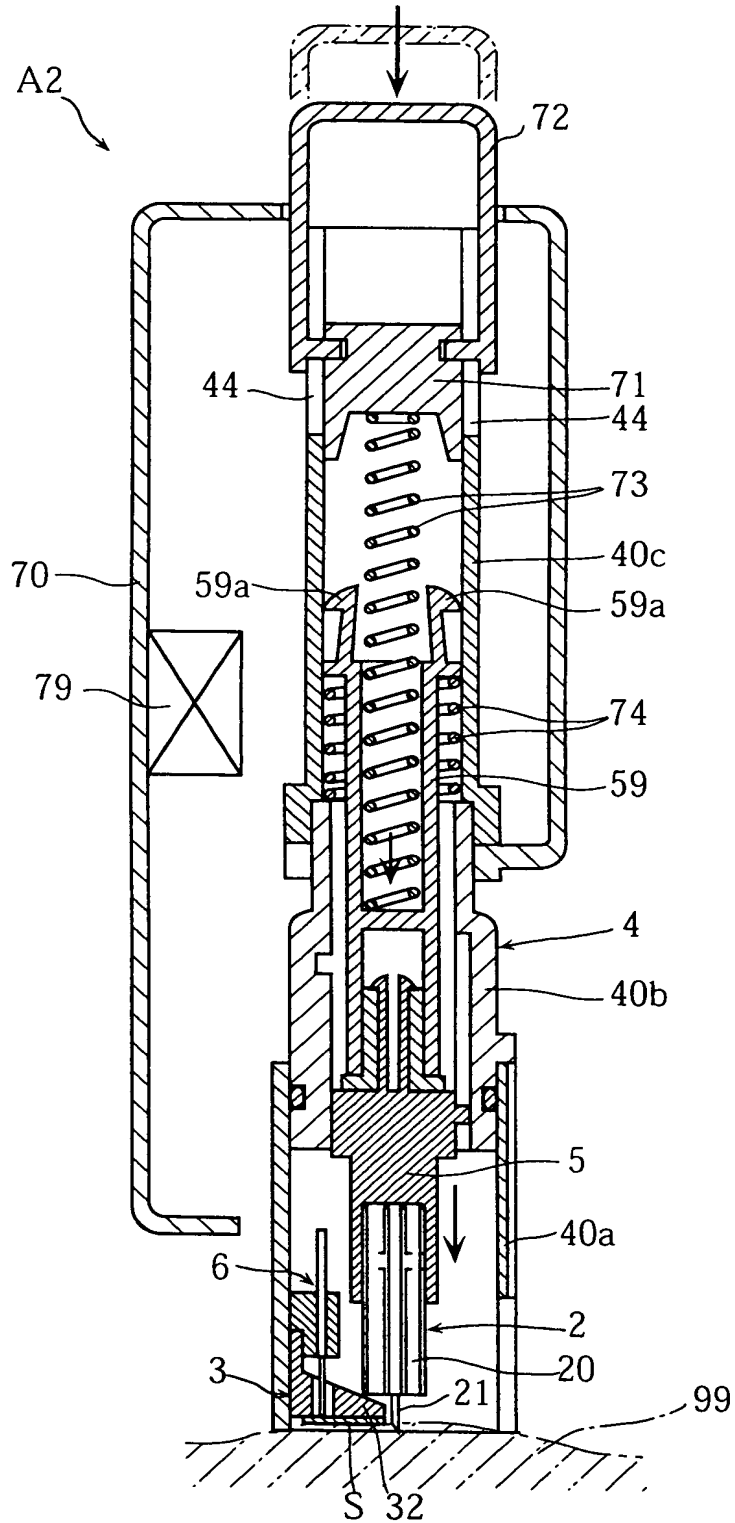


FIG.26A  
PRIOR ART

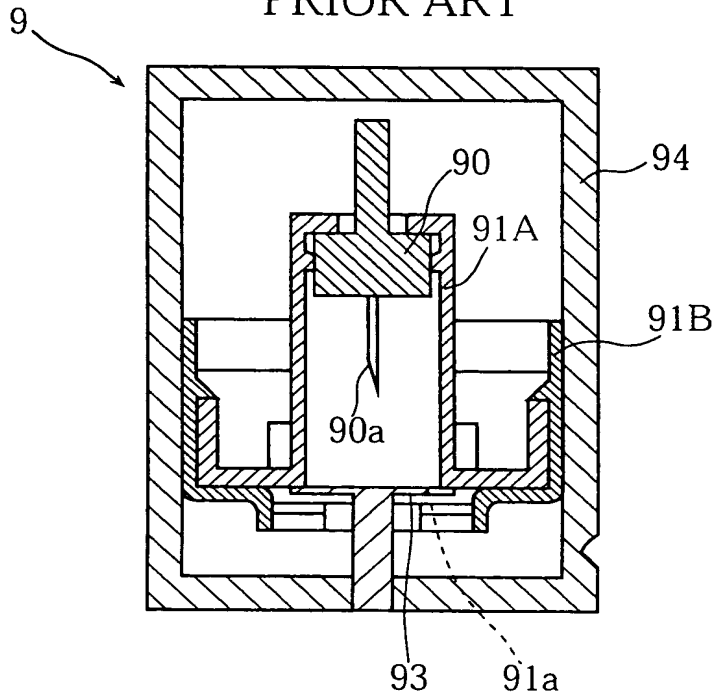


FIG.26B  
PRIOR ART

